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April 2013

# FGH50N3 300 V SMPS IGBT

### **General Description**

Using Fairchild  $^{\circledR}$ s planar technology, this IGBT is ideal for many high voltage switching applications operating at high frequencies where low conduction losses are essential. This device has been optimized for medium frequency switch mode power supplies.

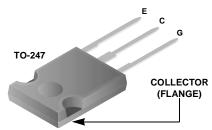
# **Applications**

• SMPS

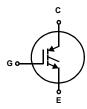
#### **Features**

- Low Saturation Voltage: VCE(sat) = 1.4 V max
- Low EOFF = 6.6 uJ/A
- SCWT = 8 us @ = 125 ℃
- 300V Switching SOA Capability
- · Positive Temperature Coefficient above 50 A

#### **Package**



### **Symbol**



## **Device Maximum Ratings** T<sub>C</sub>= 25°C unless otherwise noted

| Symbol            | Parameter   | Ratings      | Unit |
|-------------------|---|--------------|------|
| BV <sub>CES</sub> | Collector to Emitter Breakdown Voltage  | 300          | V    |
| I <sub>C25</sub>  | Collector Current Continuous, T <sub>C</sub> = 25°C   | 75           | Α    |
| I <sub>C110</sub> | Collector Current Continuous, T <sub>C</sub> = 110°C  | 75           | Α    |
| I <sub>CM</sub>   | Collector Current Pulsed (Note 1)   | 240          | Α    |
| V <sub>GES</sub>  | Gate to Emitter Voltage Continuous  | ±20          | V    |
| $V_{GEM}$         | Gate to Emitter Voltage Pulsed  | ±30          | V    |
| SSOA              | Switching Safe Operating Area at T <sub>J</sub> = 150°C, Figure 2                               | 150A at 300V |      |
| E <sub>AS</sub>   | Single Pulse Avalanche Energy, I <sub>CE</sub> = 30A, L = 1.78mH, V <sub>DD</sub> = 50V         | 800          | mJ   |
| E <sub>ARV</sub>  | Single Pulse Reverse Avalanche Energy, I <sub>EC</sub> = 30A, L = 1.78mH, V <sub>DD</sub> = 50V | 800          | mJ   |
| P <sub>D</sub>    | Power Dissipation Total T <sub>C</sub> = 25°C   | 463          | W    |
|                   | Power Dissipation Derating T <sub>C</sub> > 25°C  | 3.7          | W/°C |
| T <sub>J</sub>    | Operating Junction Temperature Range  | -55 to 150   | °C   |
| T <sub>STG</sub>  | Storage Junction Temperature Range  | -55 to 150   | °C   |
| t <sub>SC</sub>   | Short Circuit Withstand Time (Note 2)   | 8            | μs   |

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

<sup>1.</sup> Pulse width limited by maximum junction temperature.

<sup>2.</sup>  $V_{CE(PK)}$  = 180V,  $T_J$  = 125°C,  $V_{GE}$  = 12Vdc,  $R_G$  =  $5\Omega$ 

# **Package Marking and Ordering Information**

| Dev | vice Marking | Device  | Package | Tape Width | Quantity |
|-----|--------------|---------|---------|------------|----------|
|     | FGH50N3      | FGH50N3 | TO-247  | N/A        | 30       |

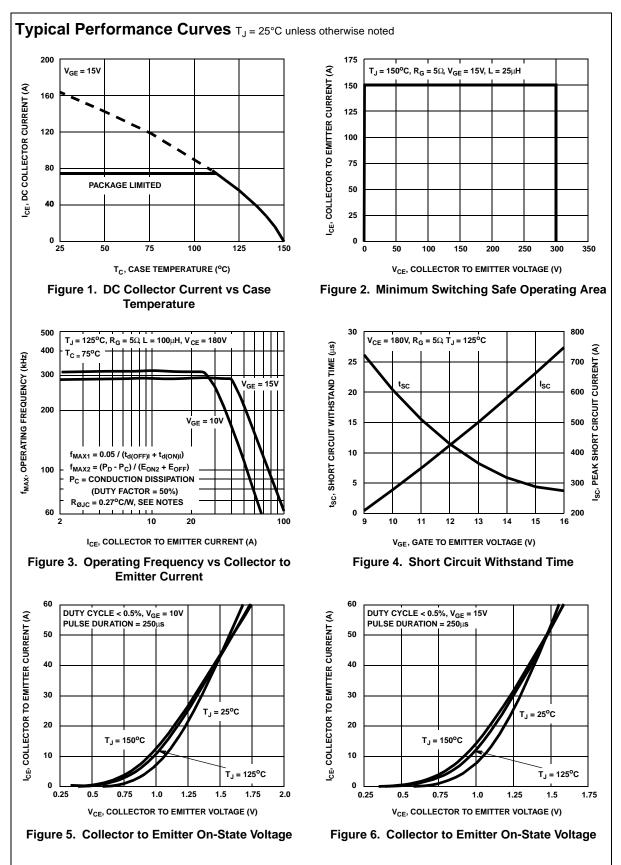
## Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

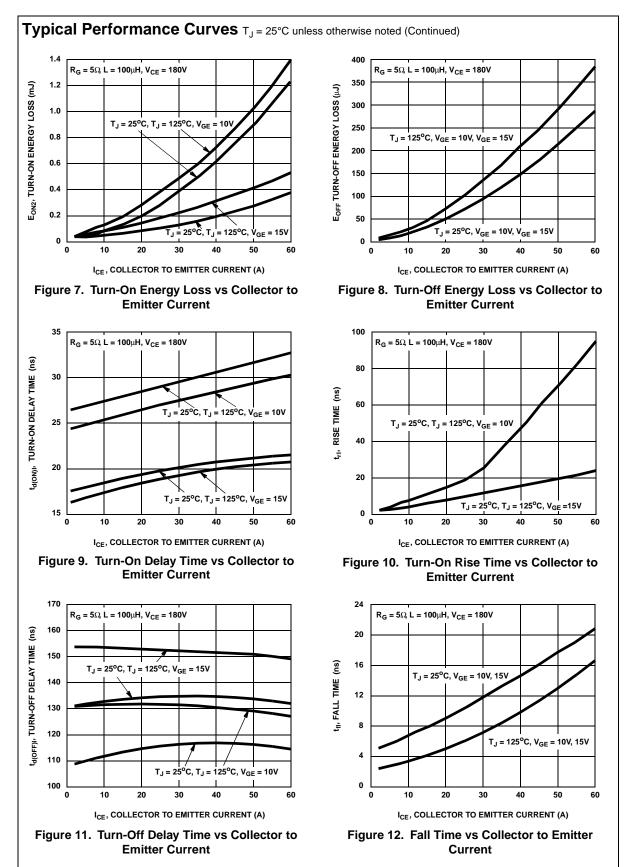
| Symbol                                  | Parameter                               | Test Co   | nditions                | Min  | Тур  | Max      | Unit |
|---|---|---|-------------------------|------|------|----------|------|
| Off State                               | Characteristics                         |   |                         |      |      |          |      |
| BV <sub>CES</sub>                       | Collector to Emitter Breakdown Voltage  | $I_{CE} = 250 \mu A, V_{CE}$  | <sub>SE</sub> = 0V      | 300V | -    | -        | V    |
| BV <sub>ECS</sub>                       | Emitter to Collector Breakdown Voltage  | $I_{EC} = 10 \text{mA}, V_G$  | E = 0V                  | 15V  | -    | -        | V    |
| I <sub>CES</sub>                        | Collector to Emitter Leakage Current    | V <sub>CE</sub> = 300V T <sub>J</sub> = 25°C  |                         | -    | -    | 250      | μΑ   |
|   |   |   | T <sub>J</sub> = 125°C  | -    | -    | 2.0      | mA   |
| I <sub>GES</sub>                        | Gate to Emitter Leakage Current         | $V_{GE} = \pm 20V$  |                         | -    | ı    | ±250     | nA   |
| On State                                | Characteristics                         |   |                         |      |      |          |      |
| V <sub>CE(SAT)</sub>                    | Collector to Emitter Saturation Voltage | I <sub>CE</sub> = 30A   | T <sub>J</sub> = 25°C   | -    | 1.30 | 1.4      | V    |
| OL(OAI)                                 |   | V <sub>GE</sub> = 15V   | T <sub>.1</sub> = 125°C | -    | 1.25 | 1.4      | V    |
|   | Characteristics                         |   |                         |      |      |          |      |
| Q <sub>G(ON)</sub>                      | Gate Charge                             | I <sub>CE</sub> = 30A   | V <sub>GE</sub> = 15V   | _    | 180  | _        | nC   |
| G(ON)                                   | Cate Charge                             |   | $V_{GF} = 20V$          | -    | 228  | _        | nC   |
| V <sub>GE(TH)</sub>                     | Gate to Emitter Threshold Voltage       | $I_{CE} = 250 \mu A, V_{CE} = V_{GE}$   |                         | 4.0  | 4.8  | 5.5      | V    |
| V <sub>GEP</sub>                        | Gate to Emitter Plateau Voltage         | $I_{CE} = 30A, V_{CE} = 150V$   |                         | -    | 7.0  | -        | V    |
| SSOA                                    | Switching SOA                           | $T_J = 150^{\circ}\text{C}, R_G = 5\Omega,$ $V_{GE} = 15V, L = 25\mu\text{H},$  |                         | 150  | -    | -        | А    |
| -                                       | Current Turn-On Delay Time              | Vce = 300V<br>IGBT and Diode at T <sub>.1</sub> = 25°C,   |                         | _    | 20   | _        | ns   |
| t <sub>d(ON)I</sub>                     | Current Rise Time                       | IGBT and Diode at $T_J$ = 25 C,<br>$I_{CE}$ = 30A,<br>$V_{CE}$ = 180V,<br>$V_{GE}$ = 15V,<br>$R_G$ = 5 $\Omega$ ,<br>$L$ = 100 $\mu$ H,<br>Test Circuit - Figure 20 |                         |      | 15   | -        | ns   |
| t <sub>rl</sub>                         | Current Turn-Off Delay Time             |   |                         |      | 135  | <u> </u> | ns   |
| t <sub>d(OFF)I</sub><br>t <sub>fl</sub> | Current Fall Time                       |   |                         | _    | 12   | _        | ns   |
| E <sub>ON2</sub>                        | Turn-On Energy (Note 1)                 |   |                         | _    | 130  | _        | μJ   |
| E <sub>OFF</sub>                        | Turn-Off Energy (Note 2)                |   |                         | _    | 92   | 120      | μJ   |
| t <sub>d(ON)I</sub>                     | Current Turn-On Delay Time              | IGBT and Diode at T <sub>.I</sub> = 125°C,  |                         | -    | 19   | -        | ns   |
| t <sub>rl</sub>                         | Current Rise Time                       | $I_{CE} = 30A$ , $V_{CE} = 180V$ , $V_{GE} = 15V$ , $R_{G} = 5\Omega$ , $L = 100\mu\text{H}$ , Test Circuit - Figure 20   |                         | _    | 13   | -        | ns   |
| t <sub>d(OFF)I</sub>                    | Current Turn-Off Delay Time             |   |                         | -    | 155  | 190      | ns   |
| t <sub>fl</sub>                         | Current Fall Time                       |   |                         | _    | 7    | 15       | ns   |
| E <sub>ON2</sub>                        | Turn-On Energy (Note 1)                 |   |                         | -    | 225  | 270      | μJ   |
| E <sub>OFF</sub>                        | Turn-Off Energy (Note 2)                |   |                         | -    | 135  | 200      | μJ   |
|   | Characteristics                         | <u> </u>  | -                       |      | ı    | 1        |      |
| R <sub>θJC</sub>                        | Thermal Resistance Junction-Case        | TO-247  |                         | _    | _    | 0.27     | °C/W |

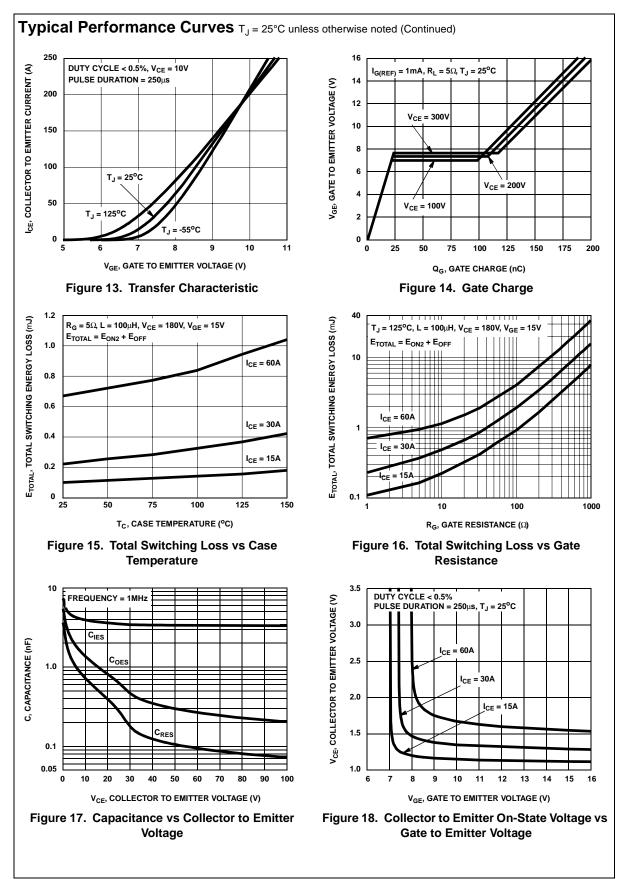
#### NOTE

 $_{\rm 1.}\,E_{\rm ON2}$  is the turn-on loss when a typical diode is used in the test circuit and the diode is at the same  $T_{\rm J}$  as the IGBT. The diode type is specified in figure 20.

<sup>2.</sup> Turn-Off Energy Loss ( $E_{OFF}$ ) is defined as the integral of the instantaneous power loss starting at the trailing edge of the input pulse and ending at the point where the collector current equals zero ( $I_{CF}$  = 0A). All devices were tested per JEDEC Standard No. 24-1 Method for Measurement of Power Device Turn-Off Switching Loss. This test method produces the true total Turn-Off Energy Loss.







## **Typical Performance Curves** T<sub>J</sub> = 25°C unless otherwise noted (Continued)

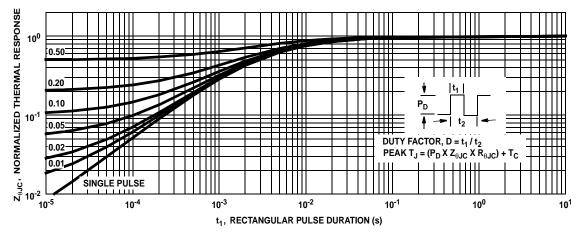


Figure 19. IGBT Normalized Transient Thermal Impedance, Junction to Case

# Test Circuit and Waveforms

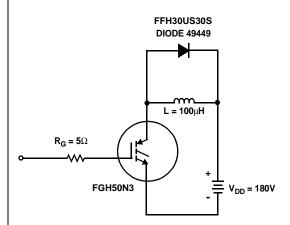


Figure 20. Inductive Switching Test Circuit

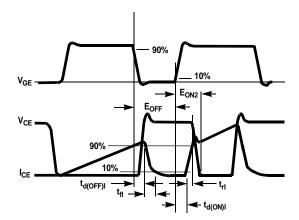


Figure 21. Switching Test Waveforms

# **Mechanical Dimensions** TO-247A03 В 15.87 E Ø 3.65 E Α ⊕ 0.254 M B AM 20.82 E 16.25 E ( 1.60 ) 3 5.56 2.66 0.254 M B AM 11.12 Ø 6.85 6.61 Ø 3.65 3.51 NOTES: UNLESS OTHERWISE SPECIFIED. 1.35 0.51 A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD 13.08 MIN FLASH, AND TIE BAR EXTRUSIONS. C. ALL DIMENSIONS ARE IN MILLIMETERS. D. DRAWING CONFORMS TO ASME Y14.5 - 1994 DOES NOT COMPLY JEDEC STANDARD VALUE E NOTCH MAY BE SQUARE G. DRAWING FILENAME: MKT-TO247A03\_REV03 3





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